

CD4009M/CD4009C Hex Buffers (Inverting) CD4010M/CD4010C Hex Buffers (Non-Inverting)

General Description

These hex buffers are monolithic complementary MOS (CMOS) integrated circuits. The N- and P-channel enhancement mode transistors provide a symmetrical circuit with output swings essentially equal to the supply voltage. This results in high noise immunity over a wide supply voltage range. No DC power other than that caused by leakage current is consumed during static conditions. All inputs are protected against static discharge. These gates may be used as hex buffers, CMOS to DTL or TTL interface or as CMOS current drivers. Conversion ranges are from 3V to 15V providing $V_{CC} \leq V_{DD}$.

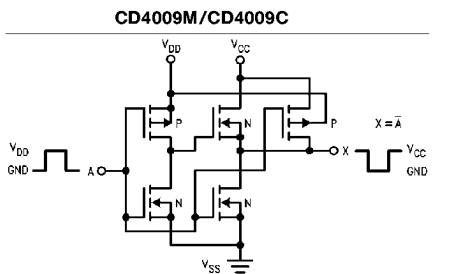
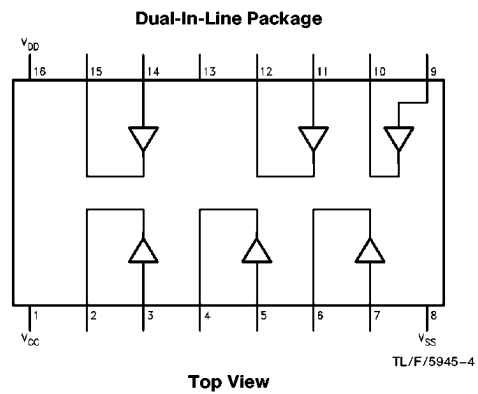
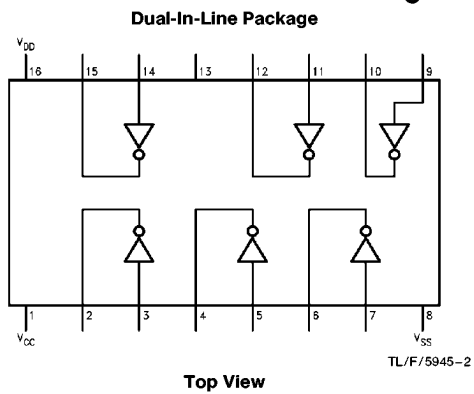
Features

- Wide supply voltage range 3.0V to 15V
- Low power 100 nW (typ.)
- High noise immunity 0.45 V_{DD} (typ.)
- High current sinking capability 8 mA (min.) at $V_O = 0.5V$ and $V_{DD} = 10V$

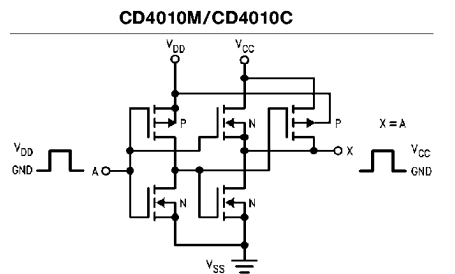
Applications

- Automotive
- Data terminals
- Instrumentation
- Medical electronics
- Alarm system
- Industrial controls
- Remote metering
- Computers

Schematic and Connection Diagrams



Hex COS/MOS to DTL or TTL converter (non-inverting).
Connect V_{CC} to DTL or TTL supply.
Connect V_{DD} to COS/MOS supply.



Hex COS/MOS to DTL or TTL converter (inverting).
Connect V_{CC} to DTL or TTL supply.
Connect V_{DD} to COS/MOS supply.

CD4009M/CD4009C Hex Buffers (Inverting)
CD4010M/CD4010C Hex Buffers (Non-Inverting)

Absolute Maximum Ratings

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Voltage at Any Pin (Note 1) $V_{SS} - 0.3V$ to $V_{SS} + 15.5V$

Operating Temperature Range

CD40XXM $-55^{\circ}C$ to $+125^{\circ}C$

CD40XXC $-45^{\circ}C$ to $+85^{\circ}C$

Storage Temperature Range (T_S) $-65^{\circ}C$ to $+150^{\circ}C$

Power Dissipation (P_D)

Dual-In-Line 700 mW

Small Outline 500 mW

Lead Temperature (T_L)

(Soldering, 10 seconds) $260^{\circ}C$

Operating Range (V_{DD})

$V_{SS} + 3V$ to $V_{SS} + 15V$

DC Electrical Characteristics

Symbol	Characteristics	Test Conditions (Volts)		Limits												Units				
				CD40XXM						CD40XXC										
				$-55^{\circ}C$		$+25^{\circ}C$		$+125^{\circ}C$		$-40^{\circ}C$		$+25^{\circ}C$		$+85^{\circ}C$						
V_O	V_{DD}	Min	Max	Min	Typ	Max	Min	Max	Min	Max	Min	Typ	Max	Min	Max					
I_{CC}	Quiescent Device Current	5	5	0.3	0.5	0.01	0.01	0.3	0.5	20	30	3	5	0.03	0.05	3	5	42	70	μA
P_D	Quiescent Device Dissipation/Package	5	10	1.5	5	0.05	0.1	1.5	5	100	300	15	50	0.15	0.5	15	50	210	700	μW
V_{OL}	Output Voltage Low Level	5	10	0.01	0.01	0	0	0.01	0.01	0.05	0.05	0.01	0.01	0	0	0.01	0.01	0.05	0.05	V
V_{OH}	Output Voltage High Level	5	10	4.99	9.99	4.99	9.99	5	10	4.95	9.95	4.99	9.99	4.99	9.99	5	10	4.95	9.95	V
V_{NL}	Noise Immunity (All Inputs)																			V
	CD4009M	$V_O \geq 4.0$	5	1	1	2.25	0.9	1	2	2.25	0.9	1	2	2.25	0.9	1	2	2.25	0.9	V
		$V_O \geq 8.0$	10	2	2	4.5	1.9	2	3	4.5	1.9	2	3	4.5	1.9	3	4.5	1.9	3	V
V_{NL}	CD4010M	$V_O \geq 1.5$	5	1.6	1.5	2.25	1.4	1.6	1.5	2.25	1.4	1.5	1.5	2.25	1.4	1.5	1.5	2.25	1.4	V
		$V_O \geq 3.0$	10	3.2	3	4.5	2.9	3.2	3	4.5	2.9	3	3	4.5	2.9	3	3	4.5	2.9	V
V_{NH}		$V_O \geq 3.5$	5	1.4	1.5	2.25	1.5	1.4	1.5	2.25	1.5	1.5	1.5	2.25	1.5	1.5	1.5	2.25	1.5	V
		$V_O \geq 7.0$	10	2.9	3	4.5	3	2.9	3	4.5	3	3	3	4.5	3	3	3	4.5	3	V
I_{DN}	Output Drive Current N-Channel (Note 2)	0.4	5	3.75	10	3	8	4	10	2.1	5.6	3.6	9.6	3	8	2.4	6.4	mA	mA	mA
I_{DP}	Output Drive Current P-Channel (Note 2)	2.5	5	-1.85	-0.9	-1.25	-0.6	-1.75	-0.8	-0.9	-0.4	-1.5	-0.72	-1.25	-0.6	-1	-0.48	mA	mA	mA
I_{IN}	Input Current							10												pA

Note 1: This device should not be connected to circuits with the power on because high transient voltage may cause permanent damage.

Note 2: I_{DN} and I_{DP} are tested one output at a time.

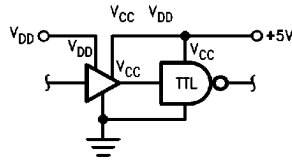
AC Electrical Characteristics*

$T_A = 25^{\circ}C$, $C_L = 15$ pF, unless otherwise noted. Typical Temperature coefficient for all values of $V_{DD} = 0.3\%/^{\circ}C$

Characteristics	Test Conditions	Limits							Units
		CD40XXM			CD40XXC				
		V_{DD} (Volts)	Min	Typ	Max	Min	Typ	Max	
Propagation Delay Time: High-to-Low Level (t_{PHL})	$V_{CC} = V_{DD}$	5	—	15	55	—	15	70	ns
	$V_{DD} = 10V$ $V_{CC} = 5V$	10	—	10	30	—	10	40	
Low-to-High Level (t_{PLH})	$V_{CC} = V_{DD}$	5	—	50	80	—	50	100	ns
	$V_{DD} = 10V$ $V_{CC} = 5V$	10	—	25	55	—	25	70	
Transition Time: High-to-Low Level (t_{THL})	$V_{CC} = V_{DD}$	5	—	20	45	—	20	60	ns
		10	—	16	40	—	16	50	
Low-to-High Level (t_{TLH})	$V_{CC} = V_{DD}$	5	—	80	125	—	80	160	ns
		10	—	50	100	—	50	120	
Input Capacitance (C_i)	Any Input		—	5	—	—	5	—	pF

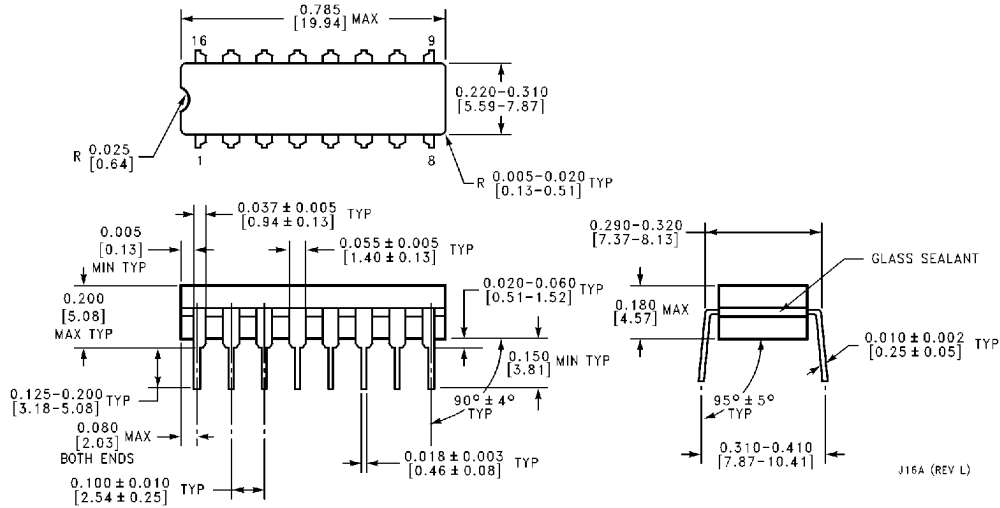
*AC Parameters are guaranteed by DC correlated testing.

Typical Application



TL/F/5945-5

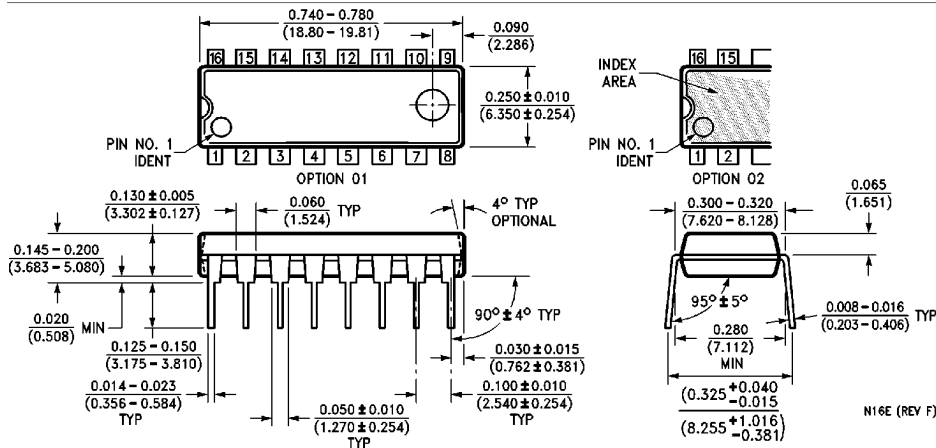
Physical Dimensions inches (millimeters)



Ceramic Dual-In-Line Package (J)
Order Number CD4009MJ, CD4009CJ, CD4010MJ or CD4010CJ
NS Package Number J16A

CD4009M/CD4009C Hex Buffers (Inverting)
CD4010M/CD4010C Hex Buffers (Non-Inverting)

Physical Dimensions inches (millimeters) (Continued)



Molded Dual-In-Line Package (N)
Order Number CD4009MN, CD4009CN, CD4010MN or CD4010CN
NS Package Number N16E

LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



National Semiconductor Corporation
 1111 West Bardin Road
 Arlington, TX 76017
 Tel: 1(800) 272-9959
 Fax: 1(800) 737-7018

National Semiconductor Europe
 Fax: (+49) 0-180-530 85 86
 Email: cnjwge@tevm2.nsc.com
 Deutsch Tel: (+49) 0-180-530 85 85
 English Tel: (+49) 0-180-532 78 32
 Français Tel: (+49) 0-180-532 93 58
 Italiano Tel: (+49) 0-180-534 16 80

National Semiconductor Hong Kong Ltd.
 13th Floor, Straight Block,
 Ocean Centre, 5 Canton Rd.
 Tsimshatsui, Kowloon
 Hong Kong
 Tel: (852) 2737-1600
 Fax: (852) 2736-9960

National Semiconductor Japan Ltd.
 Tel: 81-043-299-2309
 Fax: 81-043-299-2406

National does not assume any responsibility for use of any circuitry described, no circuit patent licenses are implied and National reserves the right at any time without notice to change said circuitry and specifications.